

IRF3710L Information



For Reference Only

Part Number IRF3710L

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 57A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF3710L Specifications

| Manufacturer Part Number IRF3710L Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 3130pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA | | |
|---|--|--------------------------------------|
| Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 130nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3130pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -5°C ~ 175°C (TI) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA | Manufacturer Part Number | IRF3710L |
| Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 130nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3130pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262-3 Long Leads, I2Pak, TO-262AA | Manufacturer | Infineon Technologies |
| Package TO-262-3 Long Leads, I2Pak, TO-262AA Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 130nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3130pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Category | Discrete Semiconductor Products |
| SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C57A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs130nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3130pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs23 mOhm @ 28A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA | | Transistors - FETs, MOSFETs - Single |
| FET Type N-Channel Nosfet (Metal Oxide) Nosfet (Me | Package | TO-262-3 Long Leads, I2Pak, TO-262AA |
| Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 130nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3130pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA | Series | HEXFET? |
| Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 57A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 100V 100V 4V @ 250µA 4V @ 250µA 130nC @ 10V 130nC @ 10V 130nC @ 10V 130nC @ 10V 20V C @ 10V 130nC @ 10V 20V Through Hole TO-262 TO-262-3 Long Leads, 12Pak, TO-262AA | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200W (Tc) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs130nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3130pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs23 mOhm @ 28A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA | Drain to Source Voltage (Vdss) | 100V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 130nC @ 10V 130nC @ 10V 3130pF @ 25V 25V 20V FET Feature - 200W (Tc) 200W (Tc) 7-5°C ~ 175°C (TJ) 7-5°C ~ 175°C (TJ) 7-262-3 Long Leads, I2Pak, TO-262AA | Current - Continuous Drain (Id) @ 25°C | 57A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 130nC @ 10V 3130pF @ 25V 220V £20V £20V Through Hole Through Hole To-262 TO-262-3 Long Leads, 12Pak, TO-262AA | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA | Vgs(th) (Max) @ Id | 4V @ 250μA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs23 mOhm @ 28A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA | Gate Charge (Qg) (Max) @ Vgs | 130nC @ 10V |
| FET Feature - 200W (Tc) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Input Capacitance (Ciss) (Max) @ Vds | 3130pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 23 mOhm @ 28A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs23 mOhm @ 28A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Power Dissipation (Max) | 200W (Tc) |
| Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Rds On (Max) @ Id, Vgs | 23 mOhm @ 28A, 10V |
| Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA | Mounting Type | Through Hole |
| | Supplier Device Package | TO-262 |
| Report errors? | Package / Case | TO-262-3 Long Leads, I2Pak, TO-262AA |
| | | Report errors? |

IRF3710L Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF3710L Payment Methods



















IRF3710L Shipping Methods













If you have any question about IRF3710L, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com